RoHS Compliant
HALOGEN-FREE

MagnaChip

MDI6N65B

N-Channel MOSFET 650V, 5.7A, 1.45Ω

General Description

The MDI6N65B use advanced Magnachip's MOSFET Technology, which provides low on-state resistance, high switching performance and excellent quality.

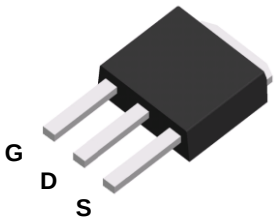
MDI6N65B is suitable device for SMPS, HID and general purpose applications.

Features

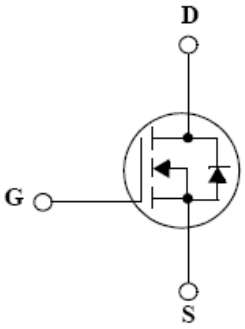
- V_{DS} = 650V
- I_D = 5.7A @V_{GS} = 10V
- $R_{DS(ON)}$ ≤ 1.45Ω @V_{GS} = 10V

Applications

- Power Supply
- PFC
- Ballast



TO-251-SS
(IPAK-SS)



Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	±30	V
Continuous Drain Current	T_C=25°C	I_D	5.7	A
	T_C=100°C		3.6	A
Pulsed Drain Current[1]		I_{DM}	22.8	A
Power Dissipation	T_C=25°C	P_D	119	W
	Derate above 25 °C		0.95	W/ °C
Peak Diode Recovery dv/dt[3]		dv/dt	4.5	V/ns
Repetitive Pulse Avalanche Energy[4]		E_{AR}	11.9	mJ
Avalanche current[1]		Iar	5.7	A
Single Pulse Avalanche Energy[4]		E_{AS}	200	mJ
Junction and Storage Temperature Range		T_J, T_{stg}	-55~150	°C

Thermal Characteristics

Characteristics	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient[1]	$R_{\theta JA}$	110	°C/W
Thermal Resistance, Junction-to-Case[1]	$R_{\theta JC}$	1.05	°C/W

Ordering Information

Part Number	Temp. Range	Package	Packing	RoHS Status
MDI6N65BTH	-55~150°C	TO-251-SS	Tube	Halogen Free

Electrical Characteristics (Ta =25°C)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	I_D = 250μA, V_{GS} = 0V	650	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	2.0	-	4.0	
Drain Cut-Off Current	I_{DSS}	V_{DS} = 600V, V_{GS} = 0V	-	-	1	μA
		V_{DS} = 650V, V_{GS} = 0V	-	-	10	
Gate Leakage Current	I_{GSS}	V_{GS} = ±30V, V_{DS} = 0V	-	-	100	nA
Drain-Source ON Resistance	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 2.8A		1.22	1.45	Ω
Forward Transconductance	g_{fs}	V_{DS} = 30V, I_D = 2.8A	-	7	-	S
Gate Input Resistance	R_g	f = 1MHz	-	8.3	-	Ω
Dynamic Characteristics						
Total Gate Charge	Q_g	V_{DS} = 520V, I_D = 6.0A, V_{GS} = 10V(3)	-	19.4	25.2	nC
Gate-Source Charge	Q_{gs}		-	3.75	-	
Gate-Drain Charge	Q_{gd}		-	8	-	
Input Capacitance	C_{iss}	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz	-	780	-	pF
Reverse Transfer Capacitance	C_{rss}		-	7	-	
Output Capacitance	C_{oss}		-	85	-	
Effective Output Capacitance Energy Related(5)	$C_{o(er)}$	V_{GS} = 0V, V_{DS} = 0V to 520V	-	26	-	pF
Effective Output Capacitance Time Related(6)	$C_{o(tr)}$		-	79	-	
Turn-On Delay Time	$t_{d(on)}$	V_{GS} = 10V, V_{DS} = 325V, I_D = 6.0A, R_G = 25Ω(3)	-	16	-	ns
Rise Time	t_r		-	30	-	
Turn-Off Delay Time	$t_{d(off)}$		-	66	140	
Fall Time	t_f		-	47	105	
Drain-Source Body Diode Characteristics						
Maximum Continuous Drain to Source Diode Forward Current	I_S	-	-	-	5.7	A
Source-Drain Diode Forward Voltage	V_{SD}	I_S = 5.7, V_{GS} = 0V	-	-	1.4	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 6.0A, dI/dt = 100A/μs	-	275	450	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	4.2	-	μC

Note :
1. Pulse width is based on R θJC & R θJA and the maximum allowed junction temperature of 150°C
2. Pulse test: pulse width ≤300us, duty cycle≤2%, pulse width limited by junction temperature $T_{J(MAX)}$=150°C
3. I_{SD} ≤5.7A, di/dt≤200A/us, V_{DD}≤BVdss, R_g =25Ω, Starting T_J=25°C
4. L=11.4mH, I_{AS}=5.7A, V_{DD}=50V, R_g =25Ω, Starting T_J=25°C
5. $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}
6. $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}

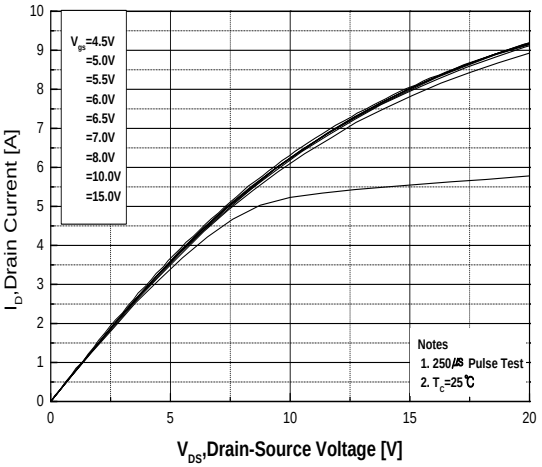


Fig.1 On-Region Characteristics

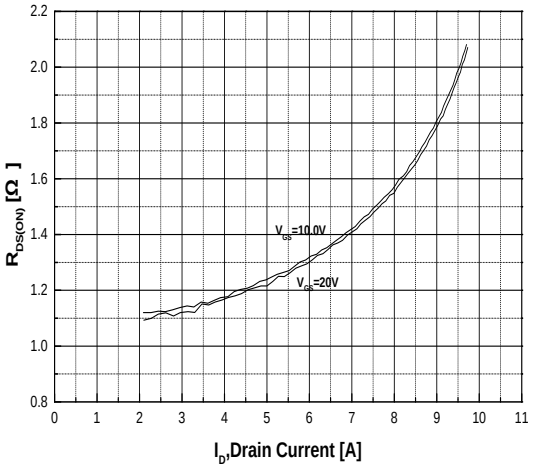


Fig.2 On-Resistance Variation with Drain Current and Gate Voltage

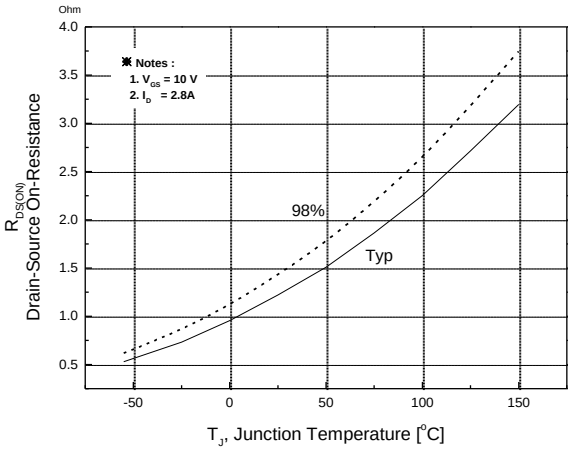


Fig.3 On-Resistance Variation with Temperature

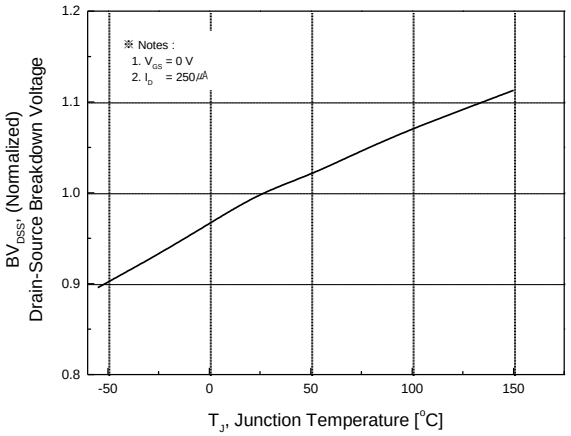


Fig.4 Breakdown Voltage Variation vs. Temperature

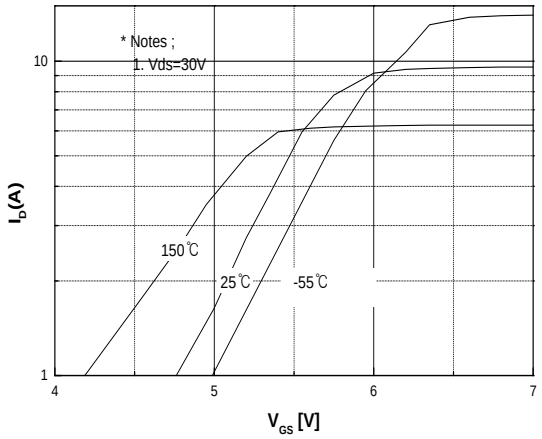


Fig.5 Transfer Characteristics

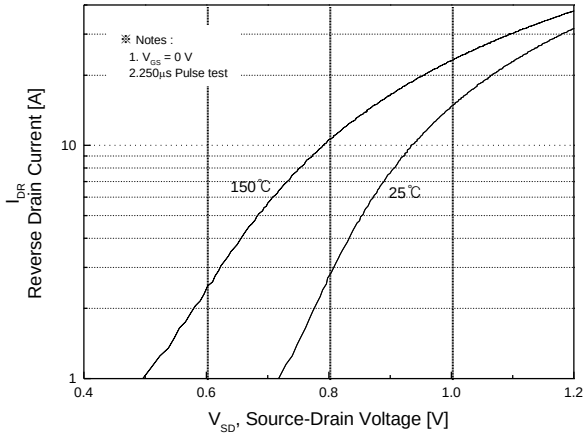


Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature

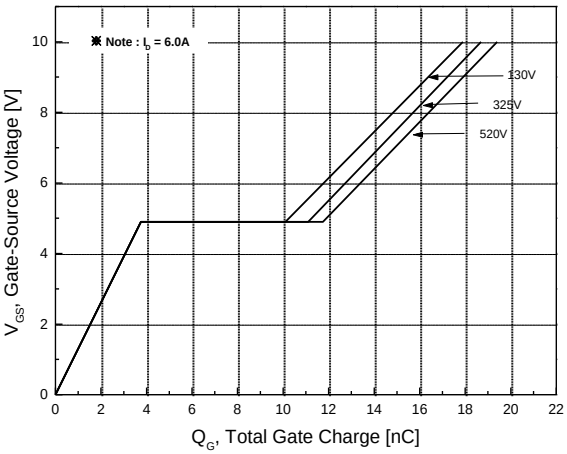


Fig.7 Gate Charge Characteristics

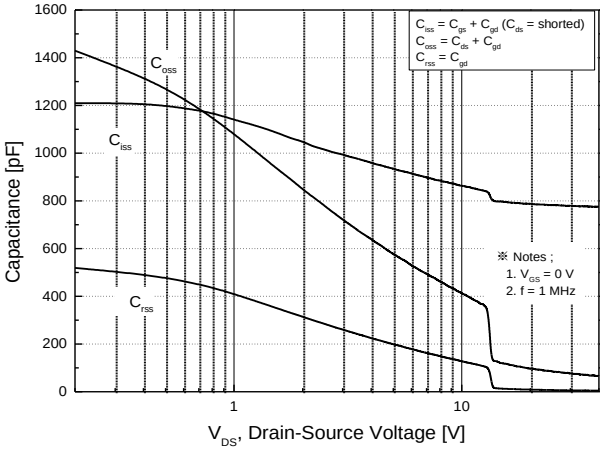


Fig.8 Capacitance Characteristics

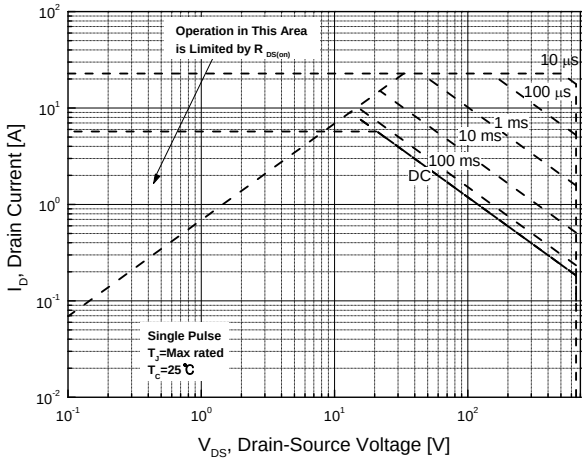


Fig.9 Maximum Safe Operating Area

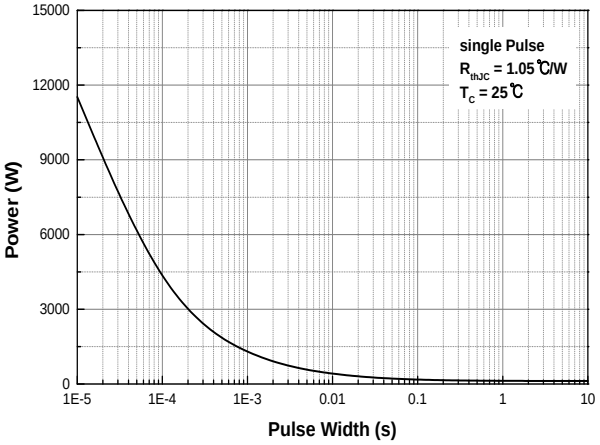


Fig.10 Single Pulse Maximum Power Dissipation

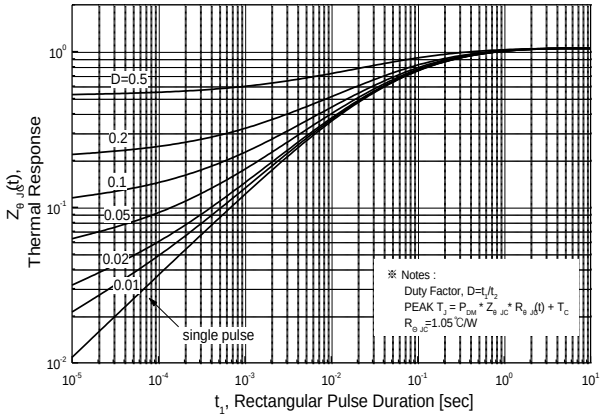


Fig.11 Transient Thermal Response Curve

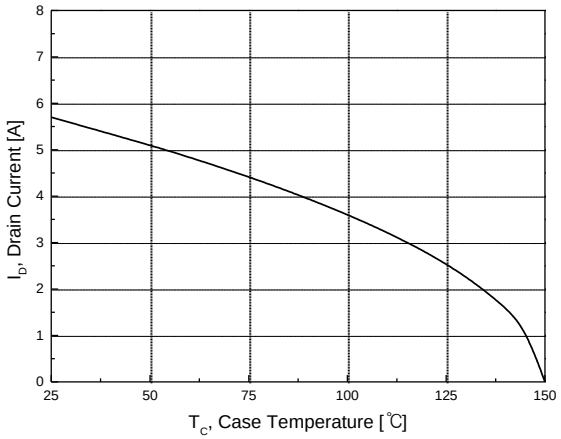
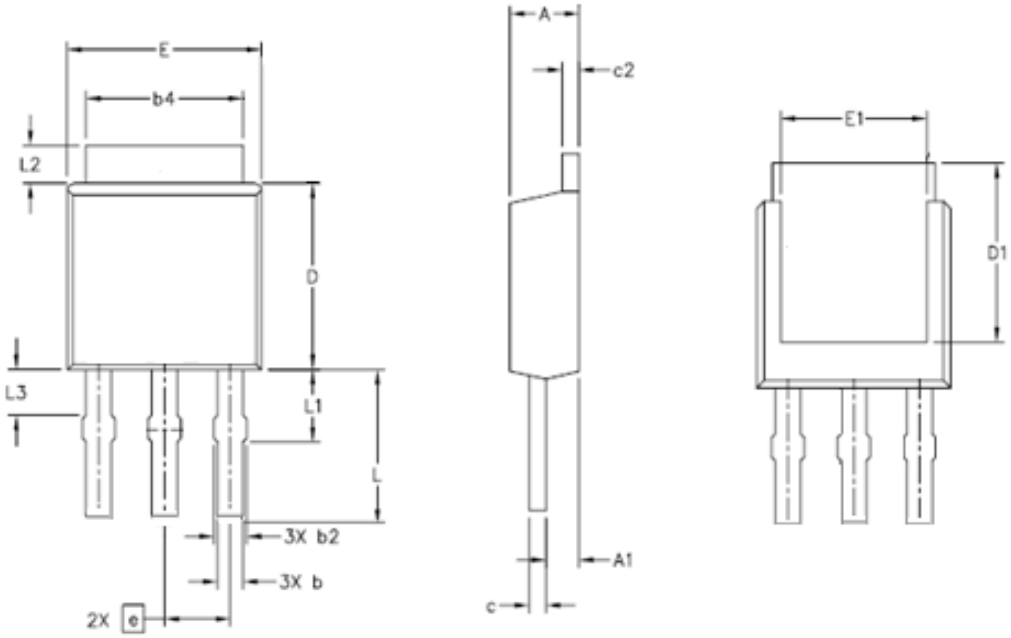


Fig.15 Maximum Drain Current vs. Case Temperature

Physical Dimension

TO-251-SS (IPAK-SS)

Dimensions are in millimeters, unless otherwise specified



Symbol	Min	Nom	Max
A	2.18	-	2.39
A1	0.89	-	1.14
b	0.64	-	0.89
b2	0.76	-	0.89
b4	4.95	-	5.46
c	0.46	-	0.60
c2	0.46	-	0.89
D	5.97	-	6.22
D1	4.75	-	-
E	6.35	-	6.73
E1	4.32	-	-
E	2.30 BSC		
L	3.20	3.35	3.50
L1	1.80	-	2.29
L2	0.70	-	1.27
L3	1.14	-	1.52

DISCLAIMER:

The Products are not designed for use in hostile environments, including, without limitation, aircraft, nuclear power generation, medical appliances, and devices or systems in which malfunction of any Product can reasonably be expected to result in a personal injury. Seller's customers using or selling Seller's products for use in such applications do so at their own risk and agree to fully defend and indemnify Seller.

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